

Features

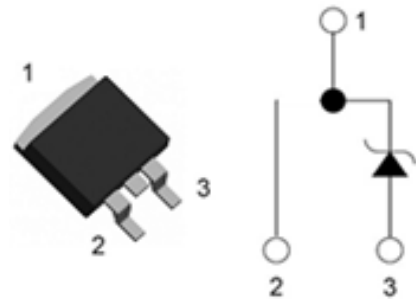
- Zero Forward/Reverse Recovery Current
- High Blocking Voltage
- High Frequency Operation
- Positive Temperature Coefficient on V_F
- Temperature Independent Switching Behavior
- High surge current capability

$V_R = 650\text{ V}$
$I_F = 10\text{ A (}T_C=150^\circ\text{C)}$
$Q_C = 23\text{ nC (}V_R=400\text{V)}$

Benefits

- Higher System Efficiency
- Parallel Device Convenience without thermal runaway
- Higher Temperature Application
- No Switching loss
- Hard Switching & Higher Reliability
- Environmental Protection

TO-263/D²PAK



Applications

- Motor Drives
- Solar
- AC/DC converters
- DC/DC converters
- Uninterruptable power supplies

Maximum Ratings ($T_C=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	Value	Unit
Peak Repetitive Reverse Voltage	V_{RRM}		650	V
Peak Reverse Surge Voltage	V_{RSM}		650	V
DC Blocking Voltage	V_R		650	V
Continuous Forward Current	I_F	$T_C=25^\circ\text{C}$	32	A
		$T_C=135^\circ\text{C}$	14	
		$T_C=150^\circ\text{C}$	10	
Non repetitive Forward Surge Current	I_{FSM}	$T_C = 25^\circ\text{C}$, $t_p=10\text{ ms}$, Half Sine Pulse	65	A
		$T_C = 110^\circ\text{C}$, $t_p=10\text{ ms}$, Half Sine Pulse	55	
		$T_C = 25^\circ\text{C}$, $t_p=10\text{ }\mu\text{s}$, Square	520	
Repetitive peak Forward Surge Current	I_{FRM}	$T_C = 25^\circ\text{C}$, $t_p=10\text{ ms}$, Freq = 0.1Hz, 100 cycles, Half Sine Pulse	55	A
		$T_C = 110^\circ\text{C}$, $t_p=10\text{ ms}$, Freq = 0.1Hz, 100 cycles, Half Sine Pulse	45	
Total power dissipation	P_D	$T_C=25^\circ\text{C}$	94	W
Operating Junction Temperature	T_J		-55 to 175	$^\circ\text{C}$
Storage Temperature	T_{STG}		-55 to 175	$^\circ\text{C}$



Electrical Characteristics

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
DC Blocking Voltage	V_{DC}	$I_R = 250\mu A, T_J = 25^\circ C$	650			V
Forward Voltage	V_F	$I_F = 10A, T_J = 25^\circ C$		1.45	1.8	V
		$I_F = 10A, T_J = 125^\circ C$		1.6		
		$I_F = 10A, T_J = 175^\circ C$		1.7		V
Reverse Current	I_R	$V_R = 650V, T_J = 25^\circ C$		12	80	μA
		$V_R = 650V, T_J = 125^\circ C$		68		μA
		$V_R = 650V, T_J = 175^\circ C$		190		μA
Total Capacitive Charge	Q_C	$V_R = 400V, I_F = 10A, di/dt = 200A/\mu s, T_J = 25^\circ C$		23		nC
Total Capacitance	C	$V_R = 1V, T_J = 25^\circ C, Freq = 1MHz$		380		pF
		$V_R = 200V, T_J = 25^\circ C, Freq = 1MHz$		48		
		$V_R = 400V, T_J = 25^\circ C, Freq = 1MHz$		31		

Note: This is a majority carrier diode, so there is no reverse recovery charge

Thermal Characteristics

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Thermal Resistance	$R_{th(j-c)}$	junction-case		1.6		$^\circ C/W$



Typical Electrical Curves

LGE3D10065E

Silicon Carbide Schottky Diode



Figure 1. Forward Characteristics

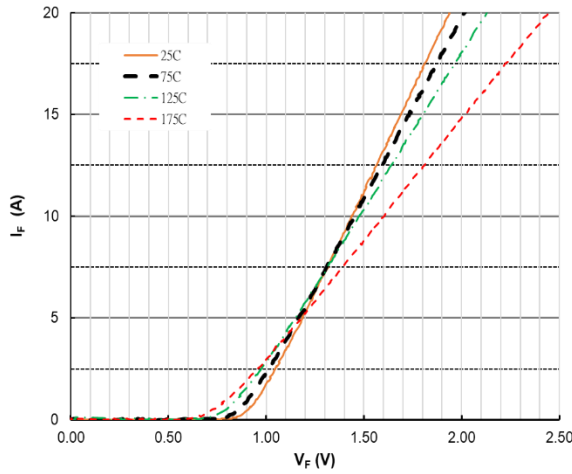


Figure 2. Forward Characteristics

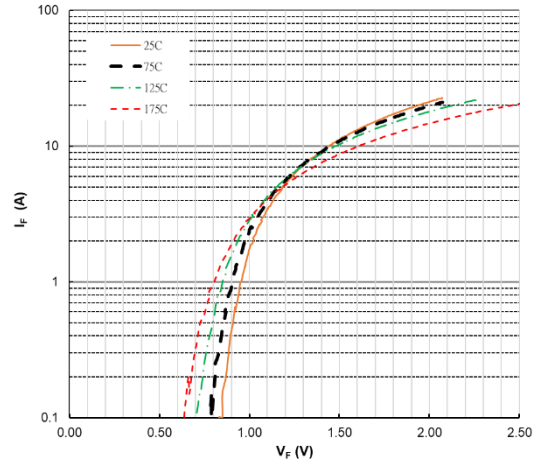


Figure 3. Reverse Characteristics

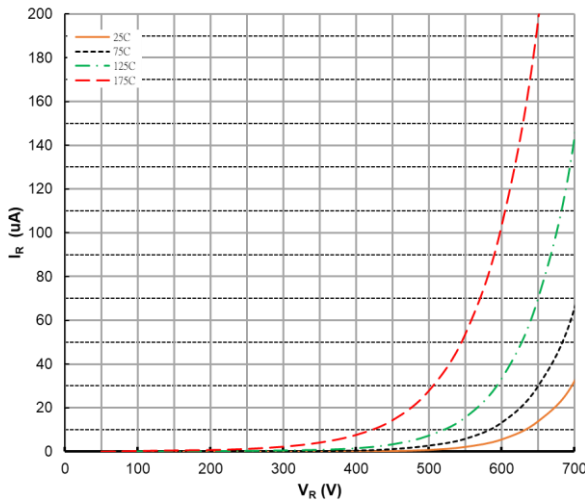


Figure 4. Power Derating

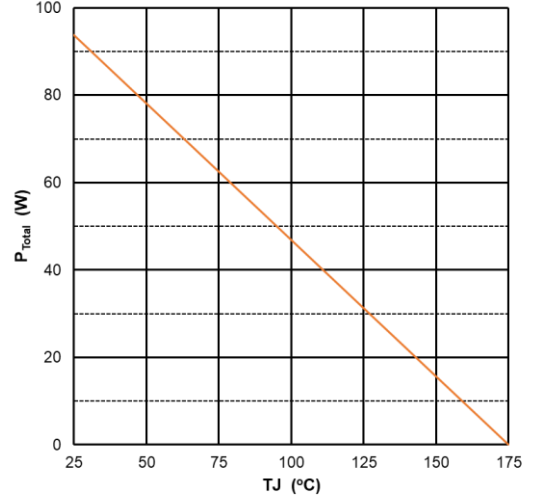


Figure 5. Capacitance vs Reverse Voltage

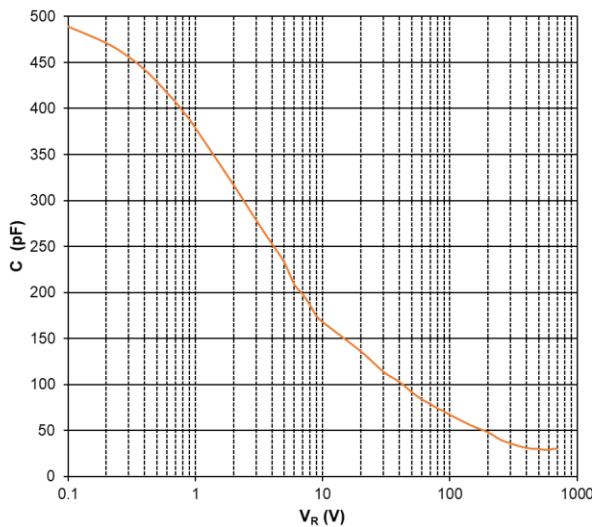
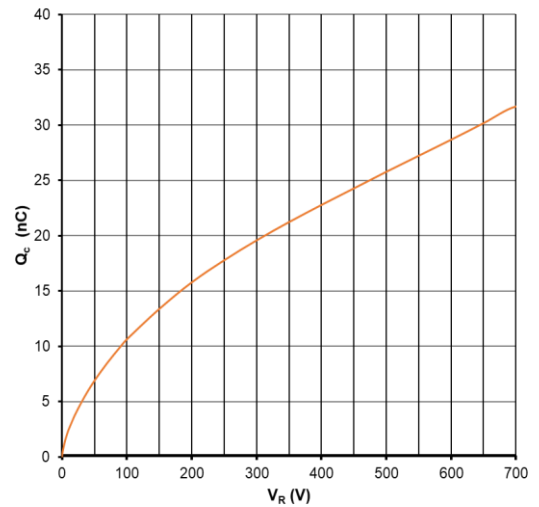


Figure 6. Recovery Charge vs Reverse Voltage



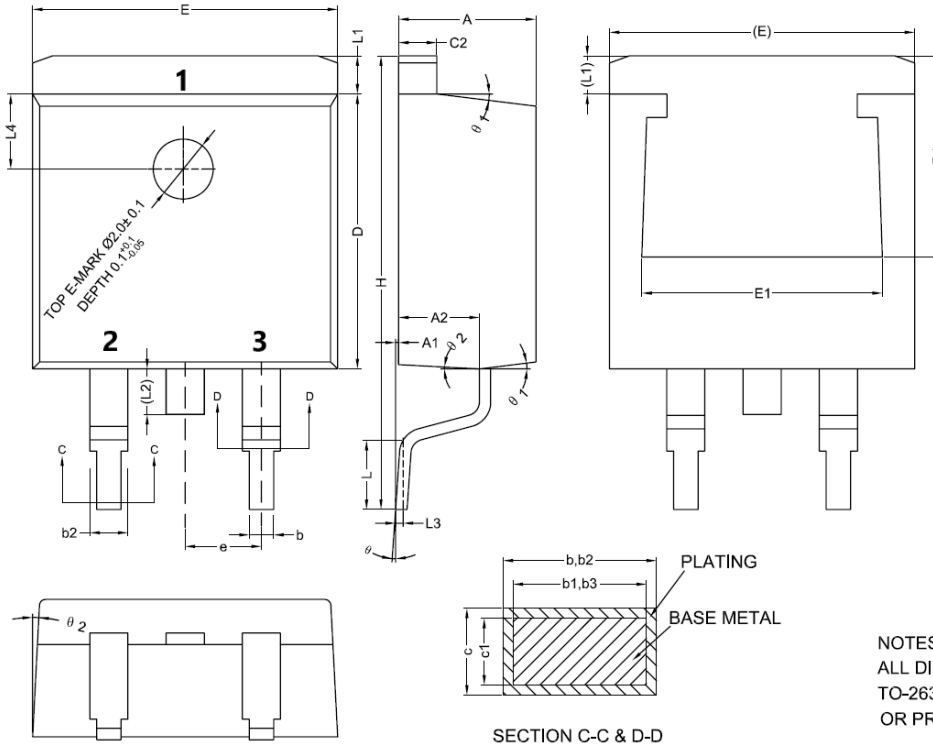


LGE3D10065E

Silicon Carbide Schottky Diode

Package Dimensions

(TO-263 / D²PAK Package)



COMMON DIMENSIONS
(UNITS OF MEASURE=MILLIMETER)

SYMBOL	MIN	NOM	MAX
A	4.40	4.57	4.70
A1	0	0.10	0.25
A2	2.59	2.69	2.79
b	0.77	-	0.90
b1	0.76	0.81	0.86
b2	1.23	-	1.36
b3	1.22	1.27	1.32
c	0.34	-	0.47
c1	0.33	0.38	0.43
c2	1.22	-	1.32
D	9.05	9.15	9.25
D1	6.60	-	-
E	10.06	10.16	10.26
E1	7.80	-	8.20
e	2.54BSC		
H	14.70	15.10	15.50
L	2.00	2.30	2.60
L1	1.17	1.27	1.40
L2	-	-	1.75
L3	0.25BSC		
L4	2.00REF		
θ	0°	-	8°
θ 1	5°	7°	9°
θ 2	1°	3°	5°

NOTES:
ALL DIMENSIONS REFER TO JEDEC STANDARD
TO-263 AB DO NOT INCLUDE MOLD FLASH
OR PROTRUSIONS.

Ordering Information

Part Number	Package	Packing	Marking	Base Quantity
LGE3D10065E	D ² PAK	Tape & Reel	LGE3D10065E	800